



MOTOROLA SEMICONDUCTORS

P.O. BOX 20912 • PHOENIX, ARIZONA 85036

The RF Line

NPN SILICON HIGH FREQUENCY TRANSISTORS

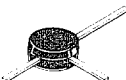
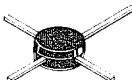
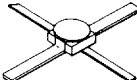
The BFR96 series transistors use the same state-of-the-art micro-wave transistor chip which features fine-line geometry, ion-implanted arsenic emitters and gold top metalization. These transistors are intended for low-to-medium power amplifiers requiring high gain, low noise figure, and low intermodulation distortion. The BFR96 and MRF961 are particularly suitable for broadband MATV/CATV amplifiers. The MRF962 uses a hermetic stripline, ceramic package and is intended for high reliability applications up to 2 GHz. The MRF965 makes an excellent VHF/UHF Class C driver amplifier for several hundred milliwatts power output.

BFR96
BFRC96
MRF961
MRF962
MRF965

$f_T = 4.5 \text{ GHz @ } 50 \text{ mA}$

**HIGH FREQUENCY
TRANSISTOR**

NPN SILICON

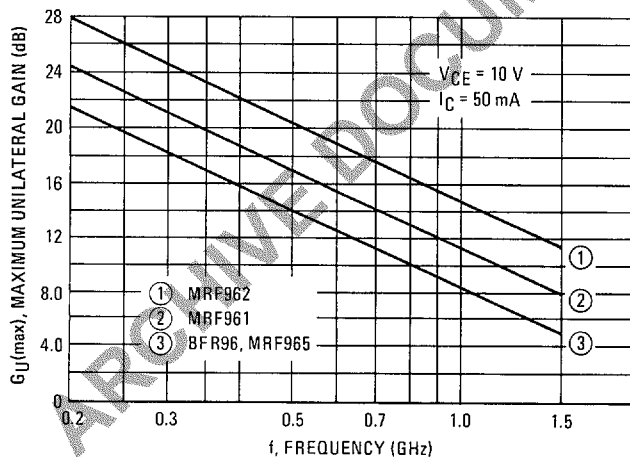
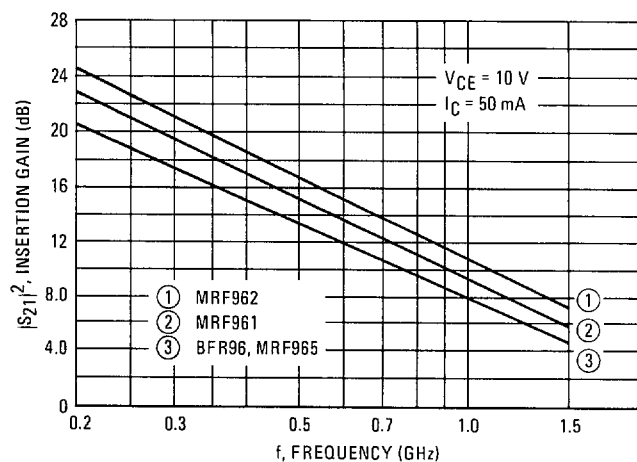
		BFRC96	BFR96	MRF961	MRF962	MRF965	
							
MAXIMUM RATINGS		Chip	Case 317A-01	Case 317-01	Case 303-01	Case 26-03	
Ratings	Symbol	Values					Unit
Collector-Emitter Voltage	V_{CEO}	15	15	15	15	15	Vdc
Collector-Base Voltage	V_{CBO}	20	20	20	20	20	Vdc
Emitter-Base Voltage	V_{EBO}	3.0	3.0	3.0	3.0	3.0	Vdc
Collector Current – Continuous	I_C	100	100	100	100	100	mAdc
Total Device Dissipation @ $T_C = 100^\circ\text{C}^{(1)}$ Derate above $T_C = 100^\circ\text{C}$	P_D	0.75 $T_J = 200^\circ\text{C}$ max	0.5 5.0	0.5 5.0	0.75 7.5	0.75 7.5	Watts mW/ $^\circ\text{C}$
Storage Temperature	T_{stg}	-65 to +200	-65 to +150	-65 to +150	-65 to +200	-65 to +200	$^\circ\text{C}$

NOTE 1. Case temperature measured on collector lead immediately adjacent to body of package.

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage ($I_C = 1.0\text{ mA}$, $I_B = 0$)	BV_{CEO}	15	—	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 100\text{ }\mu\text{A}$, $I_E = 0$)	BV_{CBO}	20	—	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 100\text{ }\mu\text{A}$, $I_C = 0$)	BV_{EBO}	3.0	—	—	Vdc
Collector Cutoff Current ($V_{CB} = 10\text{ Vdc}$, $I_E = 0$)	I_{CBO}	—	—	100	nAdc
ON CHARACTERISTICS					
DC Current Gain ($I_C = 50\text{ mA}$, $V_{CE} = 10\text{ Vdc}$)	h_{FE}	30	—	200	—
DYNAMIC CHARACTERISTICS					
Current-Gain Bandwidth Product ($I_C = 50\text{ mA}$, $V_{CE} = 10\text{ Vdc}$, $f = 0.5\text{ GHz}$)	f_T	—	4.5	—	GHz
Collector-Base Capacitance ($V_{CB} = 10\text{ Vdc}$, Emitter Guarded)	C_{cb}	—	1.2	1.5	pF
		—	1.6	2.0	
FUNCTIONAL TESTS					
Noise Figure ($I_C = 10\text{ mA}$, $V_{CE} = 10\text{ Vdc}$, $f = 0.5\text{ GHz}$)	NF	—	2.0	—	dB
Maximum Unilateral Gain/Insertion Gain ($I_C = 50\text{ mA}$, $V_{CE} = 10\text{ Vdc}$, $f = 0.5\text{ GHz}$)	$G_U(\text{max})/ S_{21} ^2$	—/12 —/13.5 —/15	14.5/13 17/15 20.5/16.5	— — —	dB

NOTE 1. $G_U(\text{max}) = \frac{|S_{21}|^2}{(1 - |S_{11}|^2)(1 - |S_{22}|^2)}$

FIGURE 1 – MAXIMUM UNILATERAL GAIN versus FREQUENCY**FIGURE 2 – $|S_{21}|^2$ versus FREQUENCY**

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A line graph showing the Maximum Unilateral Gain ($G_U(\text{max})$) in dB on the y-axis versus the Collector Current (I_C) in mA on the x-axis. The y-axis ranges from 12 to 22 dB in increments of 2. The x-axis ranges from 0 to 80 mA in increments of 20. Three curves are plotted, all for a frequency $f = 0.5 \text{ GHz}$ and a collector-emitter voltage $V_{CE} = 10 \text{ V}$. The top curve is for the MRF962, the middle for the MRF961, and the bottom for the BFR96 and MRF965. All curves show a peak in gain around 40-50 mA.

I_C (mA)	MRF962 $G_U(\text{max})$ (dB)	MRF961 $G_U(\text{max})$ (dB)	BFR96, MRF965 $G_U(\text{max})$ (dB)
10	18.0	15.5	13.2
20	19.5	16.5	13.8
30	20.5	16.8	14.0
40	20.8	17.0	14.1
50	20.8	17.0	14.1
60	20.8	16.8	14.0
70	20.5	16.5	14.0

The graph shows the f_T Gain-Bandwidth Product (GHz) on the y-axis (ranging from 2.0 to 6.0) versus I_C Collector Current (mA) on the x-axis (ranging from 0 to 100). Two curves are plotted for $V_{CE} = 5.0\text{ V}$ and $V_{CE} = 10\text{ V}$. The frequency $f = 0.5\text{ GHz}$ is indicated. The f_T for $V_{CE} = 5.0\text{ V}$ peaks at approximately 5.5 GHz around $I_C = 50\text{ mA}$. The f_T for $V_{CE} = 10\text{ V}$ peaks at approximately 4.5 GHz around $I_C = 40\text{ mA}$.

I_C (mA)	f_T (GHz) at $V_{CE} = 5.0\text{ V}$	f_T (GHz) at $V_{CE} = 10\text{ V}$
10	3.0	2.9
20	4.0	3.8
40	5.2	4.5
50	5.5	4.4
60	5.4	4.3
80	5.1	4.0
100	4.5	-

Graph showing Noise Figure (NF) in dB versus Frequency (f) in GHz for the BFR96 Series transistors. The curves are plotted for $V_{CE} = 10\text{ V}$ and $I_C = 50\text{ mA}$ (upper curve) and $I_C = 10\text{ mA}$ (lower curve). The Noise Figure increases with frequency and is higher for the higher collector current condition.

f (GHz)	NF (dB) at $I_C = 50\text{ mA}$	NF (dB) at $I_C = 10\text{ mA}$
0.1	2.5	1.8
0.2	2.6	1.85
0.3	2.7	1.9
0.5	2.9	2.1
1.0	3.5	3.1

Graph showing Noise Figure (NF) in dB versus Collector Current (I_C) in mA for the BFR96 Series. The conditions are $f = 0.5 \text{ GHz}$ and $V_{CE} = 10 \text{ V}$.

I_C (mA)	NF (dB)
5	2.2
10	2.0
20	2.2
40	2.6
60	3.0
75	3.5

The graph shows the Collector Base Capacitance (C_{cb}) in pF on the y-axis (0 to 4.0) versus the Collector Base Voltage (V_{cb}) in Vdc on the x-axis (0 to 14). Four curves are plotted, all showing a decrease in capacitance as voltage increases. The MRF965 curve is the highest, starting at approximately 3.8 pF at 0 V and decreasing to about 1.4 pF at 14 V. The 8FR96, MRF961, and MRF962 curves are clustered together, starting between 3.2 and 3.6 pF at 0 V and decreasing to about 1.0 pF at 14 V.

V_{cb} (Vdc)	MRF965 C_{cb} (pF)	8FR96, MRF961, MRF962 C_{cb} (pF)
0	3.8	3.2 - 3.6
2.0	2.5	2.2 - 2.4
4.0	2.0	1.8 - 2.0
6.0	1.7	1.5 - 1.7
8.0	1.5	1.3 - 1.5
10.0	1.4	1.2 - 1.4
12.0	1.3	1.1 - 1.3
14.0	1.4	1.0 - 1.2

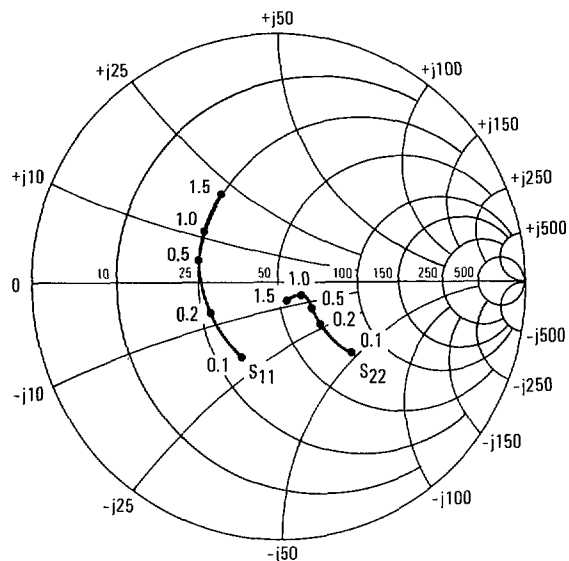
A graph showing the relationship between input power (P_{in}), output power (P_{out}), and collector efficiency (η_C) for the 2N4350 JFET. The x-axis represents P_{in} (mW) from 0 to 80. The left y-axis represents P_{out} (mW) from 100 to 500. The right y-axis represents η_C (%) from 20 to 100. Two curves are plotted: P_{out} (upper curve) and η_C (lower curve). The graph includes the following text: $f = 500 \text{ MHz}$, $V_{CE} = 12.5 \text{ V}$, and See Figure 9.

P_{in} (mW)	P_{out} (mW)	η_C (%)
10	120	25
20	180	35
30	260	42
40	340	46
50	410	48
60	450	49

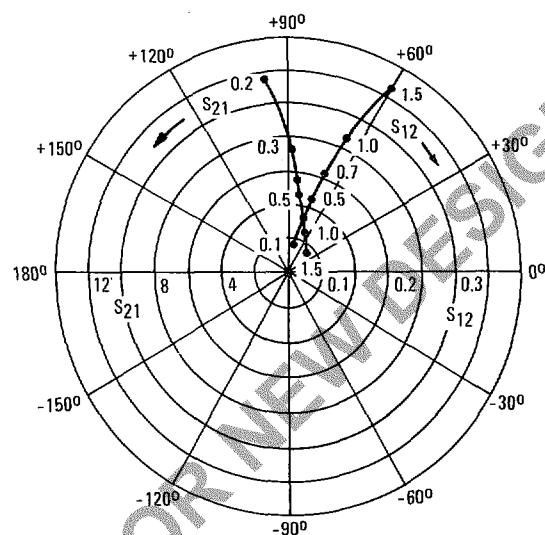
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BFR96 COMMON-EMITTER S-PARAMETERS

INPUT/OUTPUT REFLECTION
COEFFICIENTS versus FREQUENCY
($V_{CE} = 10\text{ V}$, $I_C = 50\text{ mA}$)



FORWARD/REVERSE TRANSMISSION
COEFFICIENTS versus FREQUENCY
($V_{CE} = 10\text{ V}$, $I_C = 50\text{ mA}$)

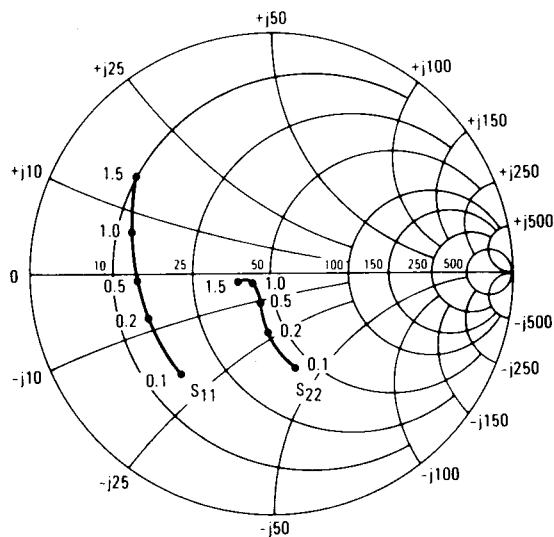


V_{CE} (Volts)	I_C (mA)	f (MHz)	S_{11}		S_{21}		S_{12}		S_{22}	
			$ S_{11} $	$\angle\phi$	$ S_{21} $	$\angle\phi$	$ S_{12} $	$\angle\phi$	$ S_{22} $	$\angle\phi$
5.0	10	100	0.51	-95	15.04	121	0.047	54	0.58	-48
		300	0.43	-163	5.87	92	0.082	58	0.26	-63
		500	0.46	174	3.61	79	0.120	63	0.19	-63
		700	0.48	162	2.65	68	0.161	63	0.15	-64
		1000	0.48	146	1.92	57	0.220	63	0.12	-79
		1500	0.54	121	1.40	43	0.320	58	0.13	-118
	25	100	0.39	-122	19.41	112	0.037	60	0.42	-68
		300	0.39	-176	6.81	89	0.079	68	0.16	-94
		500	0.42	166	4.11	78	0.129	70	0.10	-103
		700	0.44	156	3.05	69	0.176	68	0.06	-119
		1000	0.44	142	2.20	59	0.244	64	0.06	-159
		1500	0.49	118	1.62	45	0.348	57	0.10	177
	50	100	0.35	-140	21.10	106	0.032	64	0.33	-81
		300	0.38	176	7.11	88	0.081	72	0.13	-116
		500	0.42	162	4.28	78	0.133	72	0.09	-136
		700	0.43	153	3.16	70	0.183	69	0.07	-163
		1000	0.42	140	2.28	60	0.252	65	0.08	165
		1500	0.47	116	1.66	47	0.357	57	0.12	155
10	10	100	0.53	-83	15.96	124	0.039	58	0.65	-36
		300	0.38	-154	6.44	94	0.070	59	0.35	-41
		500	0.41	-179	3.98	81	0.102	64	0.30	-39
		700	0.42	166	2.94	70	0.138	65	0.27	-39
		1000	0.42	151	2.12	60	0.191	66	0.24	-47
		1500	0.49	125	1.50	44	0.278	63	0.22	-72
	25	100	0.38	-104	20.85	115	0.032	60	0.48	-48
		300	0.32	-169	7.54	91	0.070	68	0.23	-48
		500	0.35	170	4.61	80	0.109	71	0.19	-43
		700	0.37	160	3.37	70	0.152	69	0.16	-39
		1000	0.37	146	2.43	61	0.210	67	0.13	-44
		1500	0.43	121	1.73	47	0.304	61	0.10	-74
	50	100	0.33	-119	22.59	109	0.029	63	0.39	-51
		300	0.30	-176	7.74	88	0.069	72	0.19	-47
		500	0.34	166	4.70	79	0.113	73	0.16	-40
		700	0.36	158	3.45	70	0.156	70	0.14	-35
		1000	0.36	144	2.46	61	0.217	66	0.11	-39
		1500	0.42	119	1.75	47	0.310	60	0.08	-72

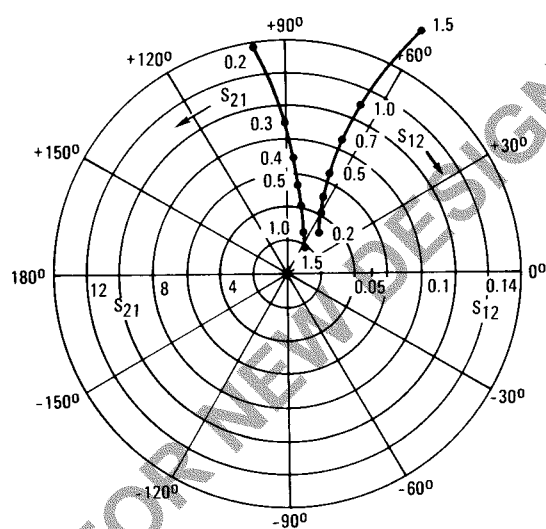


MRF961 COMMON-EMITTER S-PARAMETERS

INPUT/OUTPUT REFLECTION
COEFFICIENTS versus FREQUENCY
($V_{CE} = 10\text{ V}$, $I_C = 50\text{ mA}$)



FORWARD/REVERSE TRANSMISSION
COEFFICIENTS versus FREQUENCY
($V_{CE} = 10\text{ V}$, $I_C = 50\text{ mA}$)

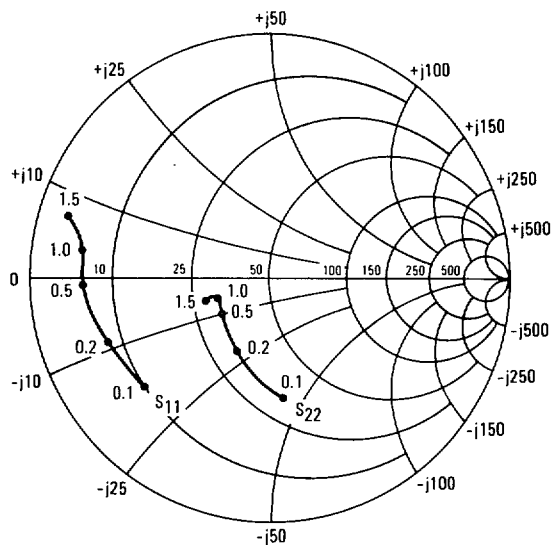


V_{CE} (Volts)	I_C (mA)	f (MHz)	S_{11}		S_{21}		S_{12}		S_{22}	
			$ S_{11} $	$\angle\phi$	$ S_{21} $	$\angle\phi$	$ S_{12} $	$\angle\phi$	$ S_{22} $	$\angle\phi$
5.0	10	100	0.65	-101	16.61	125	0.047	46	0.61	-56
		300	0.64	-160	6.61	96	0.064	39	0.27	-87
		500	0.66	-178	4.01	83	0.078	45	0.19	-98
		700	0.68	171	2.93	73	0.093	49	0.16	-108
		1000	0.68	160	2.07	63	0.119	53	0.16	-124
		1500	0.72	143	1.43	50	0.158	54	0.21	-141
	25	100	0.60	-129	22.41	115	0.034	44	0.49	-84
		300	0.63	-172	7.94	93	0.049	50	0.26	-132
		500	0.66	174	4.78	83	0.071	58	0.21	-150
		700	0.67	166	3.45	75	0.092	60	0.20	-164
		1000	0.67	156	2.46	66	0.124	61	0.21	-177
		1500	0.71	140	1.73	54	0.173	60	0.24	175
	50	100	0.59	-147	25.12	109	0.025	46	0.42	-104
		300	0.64	-178	8.47	91	0.046	60	0.28	-151
		500	0.67	171	5.05	83	0.070	65	0.26	-167
		700	0.68	164	3.67	75	0.093	65	0.25	-178
		1000	0.67	154	2.60	67	0.128	65	0.26	170
		1500	0.72	138	1.83	56	0.178	62	0.29	163
10	10	100	0.65	-90	17.47	128	0.040	50	0.67	-41
		300	0.61	-154	7.31	97	0.057	41	0.33	-57
		500	0.62	-174	4.46	84	0.069	46	0.25	-58
		700	0.64	175	3.27	74	0.084	50	0.22	-60
		1000	0.64	163	2.33	64	0.106	54	0.20	-72
		1500	0.69	145	1.56	50	0.140	57	0.22	-96
	25	100	0.57	-116	24.36	119	0.030	48	0.51	-62
		300	0.58	-167	8.10	94	0.045	52	0.20	-89
		500	0.61	178	5.43	83	0.070	58	0.14	-97
		700	0.63	169	3.93	75	0.084	60	0.10	-106
		1000	0.62	159	2.78	66	0.112	61	0.09	-124
		1500	0.67	142	1.91	53	0.156	60	0.12	-140
	50	100	0.55	-132	26.97	112	0.024	47	0.40	-73
		300	0.57	-173	9.32	91	0.042	59	0.16	-104
		500	0.60	174	5.58	82	0.064	64	0.11	-115
		700	0.62	167	4.04	74	0.086	64	0.08	-128
		1000	0.61	158	2.85	66	0.115	64	0.08	-149
		1500	0.67	141	1.96	55	0.158	61	0.12	-158

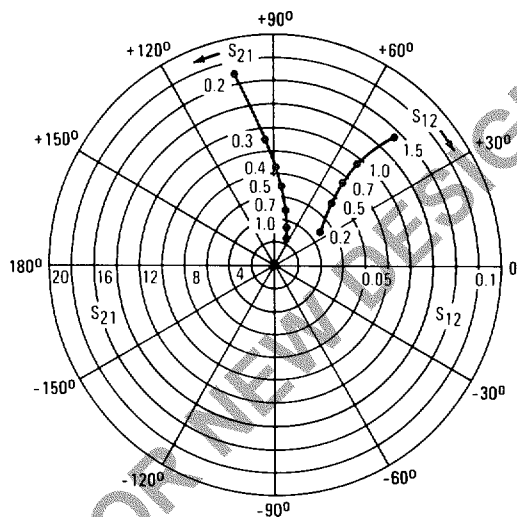


MRF962 COMMON-EMITTER S-PARAMETERS

INPUT/OUTPUT REFLECTION
COEFFICIENTS versus FREQUENCY
($V_{CE} = 10\text{ V}$, $I_C = 50\text{ mA}$)



FORWARD/REVERSE TRANSMISSION
COEFFICIENTS versus FREQUENCY
($V_{CE} = 10\text{ V}$, $I_C = 50\text{ mA}$)

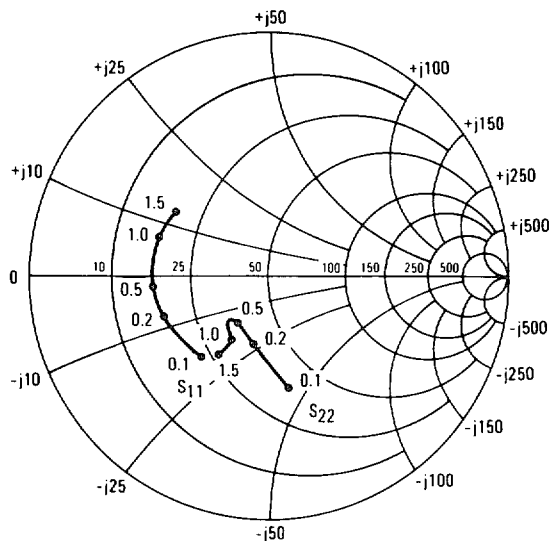


V_{CE} (Volts)	I_C (mA)	f (MHz)	S_{11}		S_{21}		S_{12}		S_{22}	
			$ S_{11} $	$\angle\phi$	$ S_{21} $	$\angle\phi$	$ S_{12} $	$\angle\phi$	$ S_{22} $	$\angle\phi$
5.0	10	100	0.70	-102	17.42	128	0.044	43	0.65	-57
		300	0.75	-156	7.11	98	0.058	24	0.32	-97
		500	0.78	-170	4.36	86	0.064	25	0.26	-110
		700	0.78	-176	3.16	77	0.071	26	0.23	-117
		1000	0.78	176	2.26	67	0.078	27	0.24	-126
		1500	0.79	167	1.51	54	0.092	29	0.31	-133
	25	100	0.69	-131	24.24	118	0.029	38	0.56	-87
		300	0.77	-167	8.76	95	0.039	32	0.35	-137
		500	0.79	-176	5.26	85	0.046	36	0.32	-150
		700	0.80	-178	3.82	78	0.055	40	0.31	-158
		1000	0.79	173	2.72	70	0.067	42	0.32	-164
		1500	0.81	164	1.82	59	0.086	42	0.34	-167
	50	100	0.71	-147	27.72	113	0.021	37	0.53	-107
		300	0.78	-173	9.59	94	0.030	40	0.41	-152
		500	0.81	179	5.72	85	0.038	46	0.39	-163
		700	0.81	176	4.09	78	0.048	50	0.38	-169
		1000	0.81	171	2.89	71	0.061	51	0.38	-175
		1500	0.82	163	1.96	62	0.082	49	0.40	-177
10	10	100	0.71	-92	18.77	131	0.037	47	0.70	-44
		300	0.74	-150	8.09	100	0.051	28	0.34	-69
		500	0.75	-166	5.01	87	0.056	28	0.27	-75
		700	0.76	-174	3.62	78	0.064	28	0.24	-79
		1000	0.76	179	2.58	69	0.071	30	0.24	-88
		1500	0.77	168	1.72	55	0.085	31	0.31	-104
	25	100	0.67	-120	27.10	122	0.027	42	0.57	-68
		300	0.73	-163	10.27	97	0.035	36	0.27	-110
		500	0.76	-174	6.21	86	0.043	39	0.22	-124
		700	0.77	-179	4.48	78	0.051	41	0.20	-132
		1000	0.77	175	3.19	71	0.062	43	0.20	-139
		1500	0.78	166	2.13	59	0.080	42	0.25	-142
	50	100	0.68	-137	31.53	116	0.020	37	0.49	-85
		300	0.74	-169	11.17	95	0.028	40	0.27	-131
		500	0.77	-177	6.69	85	0.037	46	0.24	-144
		700	0.77	178	4.82	78	0.047	48	0.23	-152
		1000	0.77	173	3.42	71	0.059	50	0.23	-158
		1500	0.79	165	2.30	61	0.078	47	0.27	-159

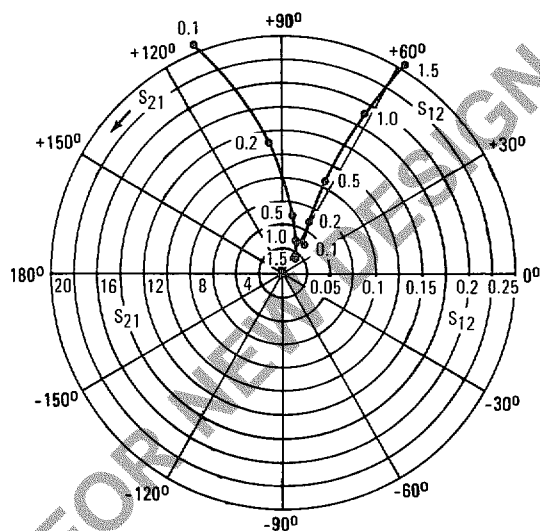


MRF965 COMMON-EMITTER S-PARAMETERS

INPUT/OUTPUT REFLECTION
COEFFICIENTS versus FREQUENCY
($V_{CE} = 10\text{ V}$, $I_C = 50\text{ mA}$)



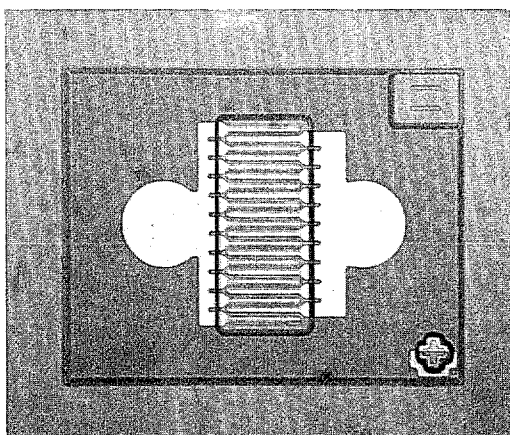
FORWARD/REVERSE TRANSMISSION
COEFFICIENTS versus FREQUENCY
($V_{CE} = 10\text{ V}$, $I_C = 50\text{ mA}$)



V_{CE} (Volts)	I_C (mA)	f (MHz)	S_{11}		S_{21}		S_{12}		S_{22}	
			$ S_{11} $	$\angle\phi$	$ S_{21} $	$\angle\phi$	$ S_{12} $	$\angle\phi$	$ S_{22} $	$\angle\phi$
5.0	10	100	0.56	-102	13.87	121	0.054	48	0.58	-62
		300	0.57	-158	5.47	90	0.084	46	0.32	-94
		500	0.56	-169	3.40	77	0.110	52	0.27	-106
		700	0.52	178	2.53	69	0.136	54	0.39	-115
		1000	0.55	167	1.79	57	0.181	56	0.35	-112
		1500	0.54	150	1.27	42	0.242	57	0.43	-122
	25	100	0.48	-129	17.61	112	0.041	51	0.47	-85
		300	0.55	-169	6.38	89	0.076	57	0.30	-125
		500	0.54	-176	3.97	77	0.111	62	0.27	-138
		700	0.50	172	2.94	71	0.114	61	0.30	-143
		1000	0.53	162	2.08	61	0.198	60	0.32	-135
		1500	0.50	146	1.50	47	0.267	57	0.37	-140
	50	100	0.47	-144	19.34	107	0.035	56	0.42	-100
		300	0.55	-173	6.72	87	0.073	63	0.31	-138
		500	0.53	-179	4.17	77	0.112	66	0.29	-150
		700	0.50	168	3.10	71	0.147	64	0.33	-153
		1000	0.53	159	2.19	62	0.206	61	0.32	-146
		1500	0.50	143	1.59	49	0.277	58	0.36	-149
10	10	100	0.56	-92	14.67	123	0.047	50	0.63	-50
		300	0.53	-152	6.00	92	0.077	47	0.34	-73
		500	0.53	-165	3.74	78	0.100	53	0.29	-82
		700	0.49	-177	2.76	70	0.124	56	0.31	-93
		1000	0.52	170	1.96	57	0.166	58	0.38	-94
		1500	0.51	153	1.36	42	0.221	59	0.46	-108
	25	100	0.46	-117	19.10	115	0.036	53	0.49	-68
		300	0.50	-164	7.09	90	0.071	57	0.26	-99
		500	0.49	-172	4.39	78	0.102	62	0.23	-110
		700	0.45	175	3.25	71	0.133	61	0.25	-119
		1000	0.49	164	2.28	60	0.181	61	0.30	-112
		1500	0.47	148	1.61	46	0.246	59	0.37	-120
	50	100	0.42	-131	20.99	110	0.033	56	0.41	-79
		300	0.49	-169	7.46	88	0.069	62	0.24	-111
		500	0.48	-175	4.63	78	0.103	65	0.21	-123
		700	0.45	172	3.40	71	0.136	64	0.25	-129
		1000	0.48	162	2.39	61	0.188	62	0.29	-119
		1500	0.45	146	1.70	48	0.251	59	0.35	-126



BFR96 CHIP TOPOGRAPHY



Nominal Chip Size: 0.014" X 0.016" X 0.005"

Front Metalization: Gold

Back Metalization: Gold

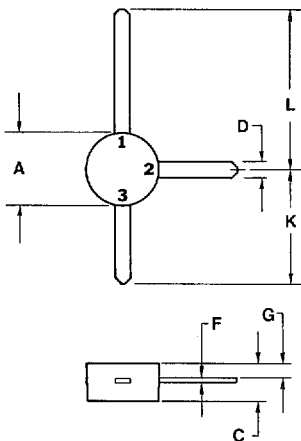
Emitter/Base Bond Pad: 2.8 mil Dia.

#Emitter Fingers: 10

#Base Fingers: 11

Emitter Diffusion: Ion-Implanted Arsenic

3-LEAD PLASTIC MACRO-T

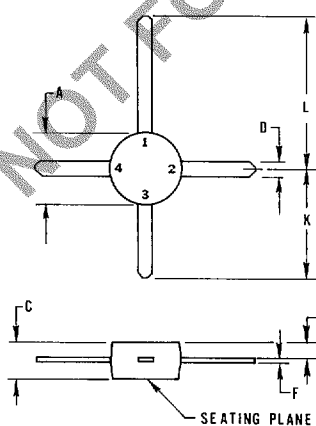


DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.44	5.21	0.175	0.205
C	1.90	2.54	0.075	0.100
D	0.84	0.99	0.033	0.039
F	0.20	0.30	0.008	0.012
G	0.76	1.14	0.030	0.045
K	7.24	8.13	0.285	0.320
L	10.54	11.43	0.415	0.450

STYLE 2:
PIN 1. COLLECTOR
2. EMITTER
3. BASE

CASE 317A-01

4 LEAD PLASTIC MACRO-T

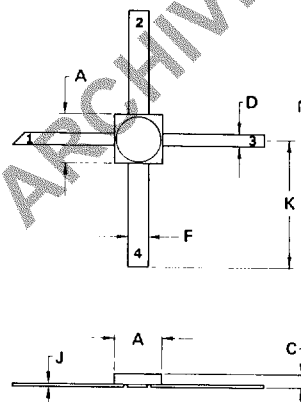


DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.44	5.21	0.175	0.205
C	1.90	2.54	0.075	0.100
D	0.84	0.99	0.033	0.039
F	0.20	0.30	0.008	0.012
G	0.76	1.14	0.030	0.045
K	7.24	8.13	0.285	0.320
L	10.54	11.43	0.415	0.450

STYLE 2:
PIN 1. COLLECTOR
2. EMITTER
3. BASE
4. EMITTER

CASE 317-01

0.100" CERAMIC STRIPLINE



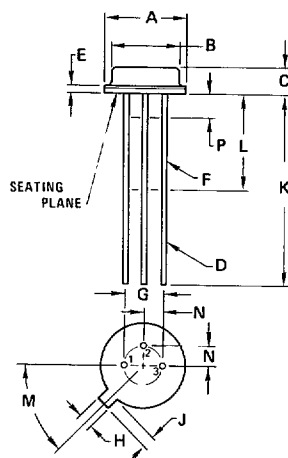
DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.29	2.67	0.090	0.105
C	0.89	1.40	0.035	0.055
D	0.41	0.61	0.016	0.024
F	0.89	1.09	0.035	0.043
J	0.08	0.15	0.003	0.006
K	4.45	5.84	0.175	0.230

NOTE:
1. DIMENSION K APPLIES TO ALL LEADS.

PIN 1. COLLECTOR
2. EMITTER
3. BASE
4. EMITTER

CASE 303-01

TO-46



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	5.31	5.84	0.209	0.230
B	4.52	4.95	0.178	0.195
C	1.65	2.16	0.065	0.085
D	0.406	0.533	0.016	0.021
E	—	1.02	—	0.040
F	0.305	0.483	0.012	0.019
G	2.54 BSC	—	0.100 BSC	—
H	0.914	1.17	0.036	0.046
J	0.711	1.22	0.028	0.048
K	12.70	—	0.500	—
L	6.35	—	0.250	—
M	45° BSC	—	45° BSC	—
N	1.27 BSC	—	0.050 BSC	—
P	—	1.27	—	0.050

All JEDEC dimensions and notes apply

PIN 1. EMITTER
2. BASE
3. COLLECTOR

CASE 26-03


MOTOROLA Semiconductor Products Inc.

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